Title (en)

Integrated circuit with closely coupled high-voltage output and offline transistor pair.

Title (de)

Integrierter Schaltkreis mit enggekoppeltem Hochspannungsausgang und "Offline" Transistorpaar

Title (fr)

Circuit intégré comportant une paire de transistors à haute tension de sortie et "offline" étroitement couplée

Publication

EP 1309006 B1 20090617 (EN)

Application

EP 02255727 A 20020816

Priority

US 5353801 A 20011102

Abstract (en)

[origin: EP1309006A2] An integrated circuit fabricated in a single silicon substrate includes a high-voltage output transistor having source and drain regions separated by a channel region, and a gate disposed over the channel region. Also included is an offline transistor having source and drain regions separated by a channel region and a gate disposed over the channel region of the offline transistor. A drain electrode is commonly coupled to the drain region of the high-voltage output transistor and to the drain region of the offline transistor.

IPC 8 full level

H01L 21/822 (2006.01); **H01L 27/07** (2006.01); **H01L 21/8234** (2006.01); **H01L 27/04** (2006.01); **H01L 27/088** (2006.01); **H01L 29/06** (2006.01)

CPC (source: EP US)

H01L 27/0705 (2013.01 - EP US); H01L 2224/05553 (2013.01 - EP US); H01L 2224/05554 (2013.01 - EP US); H01L 2224/49113 (2013.01 - EP US); H01L 2924/13091 (2013.01 - EP US)

Designated contracting state (EPC)

AT BE BG CH CY CZ DE DK EE ES FI FR GB GR IE IT LI LU MC NL PT SE SK TR

DOCDB simple family (publication)

EP 1309006 A2 20030507; **EP 1309006 A3 20070822**; **EP 1309006 B1 20090617**; AT E434267 T1 20090715; DE 60232635 D1 20090730; EP 2093799 A2 20090826; EP 2093799 A3 20100310; JP 2003264241 A 20030919; JP 4125567 B2 20080730; US 2003112052 A1 20030619; US 6552597 B1 20030422; US 6734714 B2 20040511

DOCDB simple family (application)

EP 02255727 A 20020816; AT 02255727 T 20020816; DE 60232635 T 20020816; EP 09162684 A 20020816; JP 2002258267 A 20020731; US 35478803 A 20030130; US 5353801 A 20011102